

HD34387

MEMS Band Pass Filter

Features:

- Pass Band : 2.6G~ 4.0 GHz
- Insertion Loss : 3.0dB
- Size : 7.67x11.0x0.5mm

Absolute Maximum Ratings

- Max. Input Power : +35dBm
- Storage Temperature : -55 ~ +85Deg.C
- Operating Temperature : -55 ~ +125Deg.C



ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS

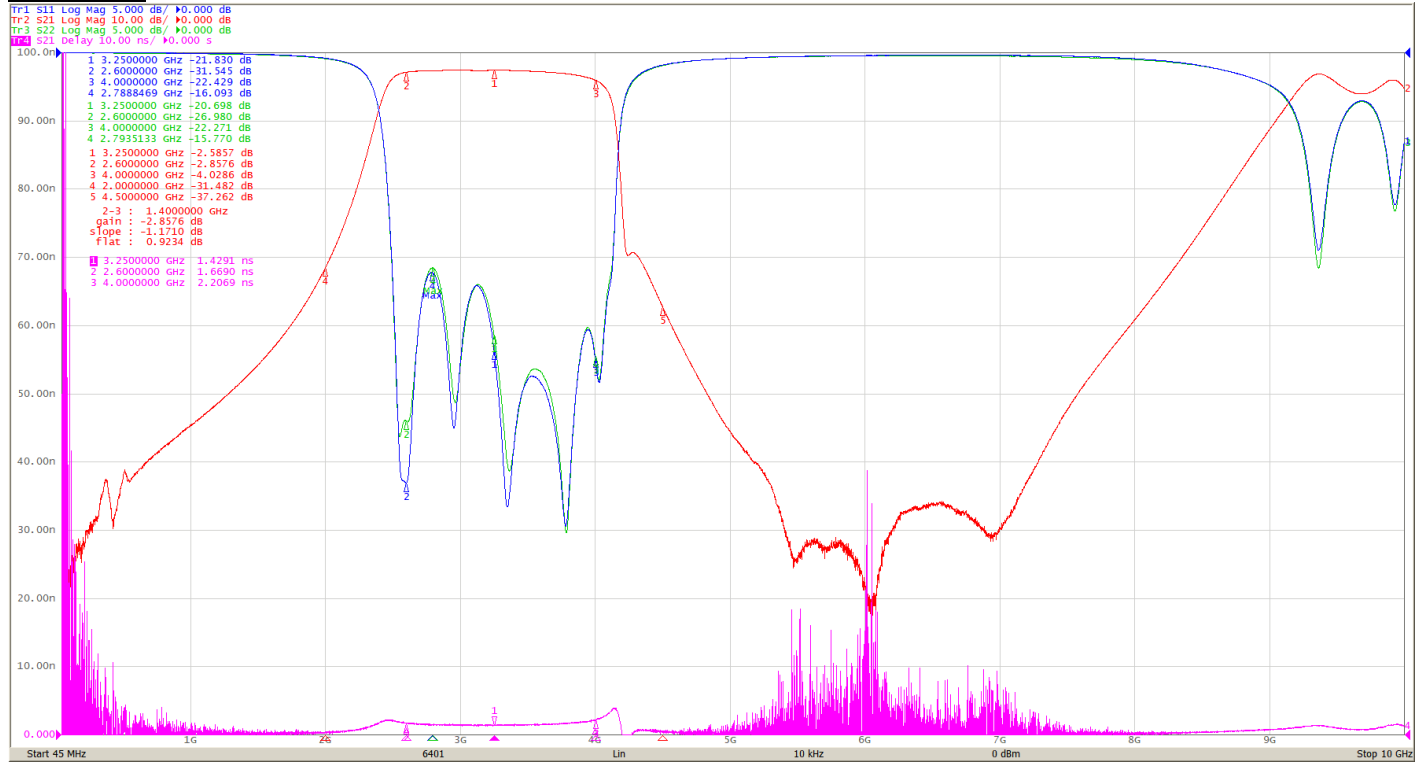
Electrical Specifications (TA=+25Deg.C, 50Ω system)

Parameter	Min.Value	Typical Value	Max.Value	Unit	
Frequency Range	2.6 ~ 4.0			GHz	
Insertion Loss (Fc)	-	2.58	3.0	dB	
Ripple	-	0.92	1.3	dB	
Attenuation	DC~@2GHz	30.0	31.48	-	dB
	@4.5GHz ~ 8GHz	30.0	37.26	-	dB
Return Loss	15.0	15.77	-	dB	
Group Delay	-	2.20	4.0	ns	

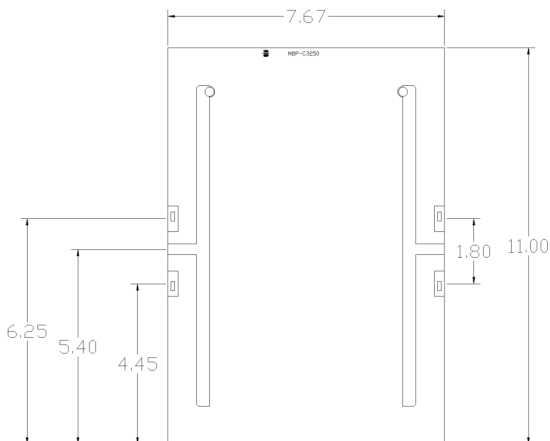
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Test Curve



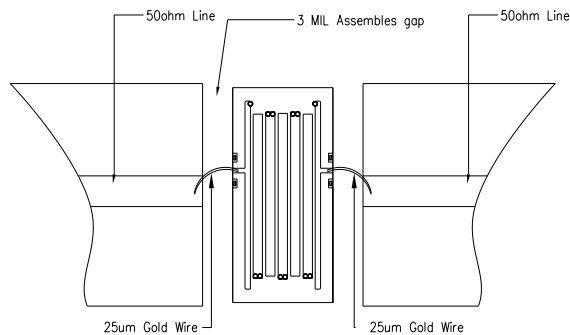
Size



- Remarks: Unit : mm, Tolerance : ±0.25mm
1. Chip bottom is gold plated and grounded.
 2. Bonding pressure points are gold plated.
 3. Don't bond on the through holes.

Applications

1. Assembly and Bonding Diagram. (Reference)



Assembly Diagram

2. The chip is back-metalized and can be die mounted with AuSn eutectic performs or with electrically conductive epoxy (for example ME8456).
3. The die should be assembled on carriers like Kovar or Mu-Cu which have same Coefficient of thermal expansion. (2.9ppm/°C) with Silicon, thickness 0.2mm max.
4. Handle the chips in a clean environment. DO NOT attempt to clean the chip using liquid cleaning systems.
5. Handle the chip along the edges with a vacuum collet or with a sharp pair of bent tweezers.